

MOSFET

OptiMOS™ 5 Power-Transistor, 80 V

Features

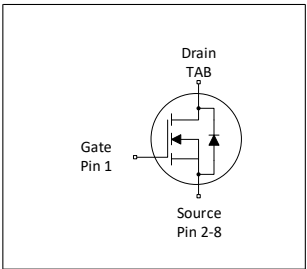
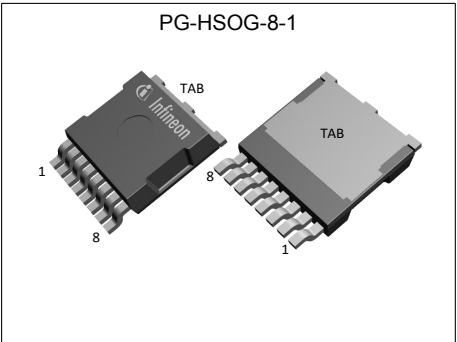
- N-channel, normal level
- Very low on-resistance  $R_{DS(on)}$
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Ideal for high frequency switching and sync. rec.

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

| Parameter        | Value | Unit |
|------------------|-------|------|
| $V_{DS}$         | 80    | V    |
| $R_{DS(on),max}$ | 2.5   | mΩ   |
| $I_D$            | 184   | A    |
| $Q_{oss}$        | 83    | nC   |
| $Q_G$            | 70    | nC   |



RoHS

| Type / Ordering Code | Package     | Marking  | Related Links |
|----------------------|-------------|----------|---------------|
| IPTG025N08NM5        | PG-HSOG-8-1 | 025N08N5 | -             |

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                    | Symbol            | Values |      |                         | Unit | Note / Test Condition                                                                                                                                                                                              |
|----------------------------------------------|-------------------|--------|------|-------------------------|------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                              |                   | Min.   | Typ. | Max.                    |      |                                                                                                                                                                                                                    |
| Continuous drain current <sup>1)</sup>       | $I_D$             | -      | -    | 184<br>130<br>103<br>28 | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=6\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=40\text{ °C/W}^{2)}$ |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$     | -      | -    | 736                     | A    | $T_A=25\text{ °C}$                                                                                                                                                                                                 |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$          | -      | -    | 124                     | mJ   | $I_D=150\text{ A}$ , $R_{GS}=25\text{ }\Omega$                                                                                                                                                                     |
| Gate source voltage                          | $V_{GS}$          | -20    | -    | 20                      | V    | -                                                                                                                                                                                                                  |
| Power dissipation                            | $P_{tot}$         | -      | -    | 167<br>3.8              | W    | $T_C=25\text{ °C}$<br>$T_A=25\text{ °C}$ , $R_{thJA}=40\text{ °C/W}^{2)}$                                                                                                                                          |
| Operating and storage temperature            | $T_j$ , $T_{stg}$ | -55    | -    | 175                     | °C   | IEC climatic category; DIN IEC 68-1: 55/175/56                                                                                                                                                                     |

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter                                                               | Symbol     | Values |      |      | Unit | Note / Test Condition |
|-------------------------------------------------------------------------|------------|--------|------|------|------|-----------------------|
|                                                                         |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case                                     | $R_{thJC}$ | -      | 0.55 | 0.9  | °C/W | -                     |
| Thermal resistance, junction - ambient, 6 cm <sup>2</sup> cooling area  | $R_{thJA}$ | -      | -    | 40   | °C/W | -                     |
| Thermal resistance, junction - ambient, minimal footprint <sup>2)</sup> | $R_{thJA}$ | -      | -    | 62   | °C/W | -                     |

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

| Parameter                        | Symbol        | Values |             |            | Unit          | Note / Test Condition                                                                                                               |
|----------------------------------|---------------|--------|-------------|------------|---------------|-------------------------------------------------------------------------------------------------------------------------------------|
|                                  |               | Min.   | Typ.        | Max.       |               |                                                                                                                                     |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 80     | -           | -          | V             | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                                                                                             |
| Gate threshold voltage           | $V_{GS(th)}$  | 2.2    | 3           | 3.8        | V             | $V_{DS}=V_{GS}$ , $I_D=108\text{ }\mu\text{A}$                                                                                      |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | 0.1<br>10   | 1<br>100   | $\mu\text{A}$ | $V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$<br>$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | 10          | 100        | nA            | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                                                                                          |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 2.25<br>3.0 | 2.5<br>3.8 | m $\Omega$    | $V_{GS}=10\text{ V}$ , $I_D=150\text{ A}$<br>$V_{GS}=6\text{ V}$ , $I_D=75\text{ A}$                                                |
| Gate resistance <sup>1)</sup>    | $R_G$         | -      | 1.5         | 2.25       | $\Omega$      | -                                                                                                                                   |
| Transconductance                 | $g_{fs}$      | 85     | 170         | -          | S             | $ V_{DS} \geq 2 I_D /R_{DS(on)max}$ , $I_D=100\text{ A}$                                                                            |

**Table 5 Dynamic characteristics**

| Parameter                                  | Symbol       | Values |      |      | Unit | Note / Test Condition                                                                               |
|--------------------------------------------|--------------|--------|------|------|------|-----------------------------------------------------------------------------------------------------|
|                                            |              | Min.   | Typ. | Max. |      |                                                                                                     |
| Input capacitance <sup>1)</sup>            | $C_{iss}$    | -      | 4900 | 6500 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$                                       |
| Output capacitance <sup>1)</sup>           | $C_{oss}$    | -      | 790  | 1100 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$                                       |
| Reverse transfer capacitance <sup>1)</sup> | $C_{rss}$    | -      | 36   | 63   | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$                                       |
| Turn-on delay time                         | $t_{d(on)}$  | -      | 20   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ ,<br>$R_{G,ext}=1.8\text{ }\Omega$ |
| Rise time                                  | $t_r$        | -      | 12   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ ,<br>$R_{G,ext}=1.8\text{ }\Omega$ |
| Turn-off delay time                        | $t_{d(off)}$ | -      | 42   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ ,<br>$R_{G,ext}=1.8\text{ }\Omega$ |
| Fall time                                  | $t_f$        | -      | 13   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ ,<br>$R_{G,ext}=1.8\text{ }\Omega$ |

**Table 6 Gate charge characteristics<sup>2)</sup>**

| Parameter                          | Symbol        | Values |      |      | Unit | Note / Test Condition                                                        |
|------------------------------------|---------------|--------|------|------|------|------------------------------------------------------------------------------|
|                                    |               | Min.   | Typ. | Max. |      |                                                                              |
| Gate to source charge              | $Q_{gs}$      | -      | 24   | -    | nC   | $V_{DD}=40\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge at threshold           | $Q_{g(th)}$   | -      | 14.6 | -    | nC   | $V_{DD}=40\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge <sup>1)</sup> | $Q_{gd}$      | -      | 15.1 | 22.8 | nC   | $V_{DD}=40\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Switching charge                   | $Q_{sw}$      | -      | 24   | -    | nC   | $V_{DD}=40\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total <sup>1)</sup>    | $Q_g$         | -      | 70   | 87   | nC   | $V_{DD}=40\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate plateau voltage               | $V_{plateau}$ | -      | 4.8  | -    | V    | $V_{DD}=40\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total, sync. FET       | $Q_{g(sync)}$ | -      | 60   | -    | nC   | $V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$                     |
| Output charge <sup>1)</sup>        | $Q_{oss}$     | -      | 83   | 110  | nC   | $V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$                                   |

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

| Parameter                             | Symbol        | Values |      |      | Unit | Note / Test Condition                                                       |
|---------------------------------------|---------------|--------|------|------|------|-----------------------------------------------------------------------------|
|                                       |               | Min.   | Typ. | Max. |      |                                                                             |
| Diode continuous forward current      | $I_S$         | -      | -    | 127  | A    | $T_C=25\text{ °C}$                                                          |
| Diode pulse current                   | $I_{S,pulse}$ | -      | -    | 736  | A    | $T_C=25\text{ °C}$                                                          |
| Diode forward voltage                 | $V_{SD}$      | -      | 0.93 | 1.2  | V    | $V_{GS}=0\text{ V}$ , $I_F=100\text{ A}$ , $T_J=25\text{ °C}$               |
| Reverse recovery time <sup>1)</sup>   | $t_{rr}$      | -      | 84   | 168  | ns   | $V_R=40\text{ V}$ , $I_F=100\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge <sup>1)</sup> | $Q_{rr}$      | -      | 175  | 350  | nC   | $V_R=40\text{ V}$ , $I_F=100\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$ |

<sup>1)</sup> Defined by design. Not subject to production test.

## 4 Electrical characteristics diagrams

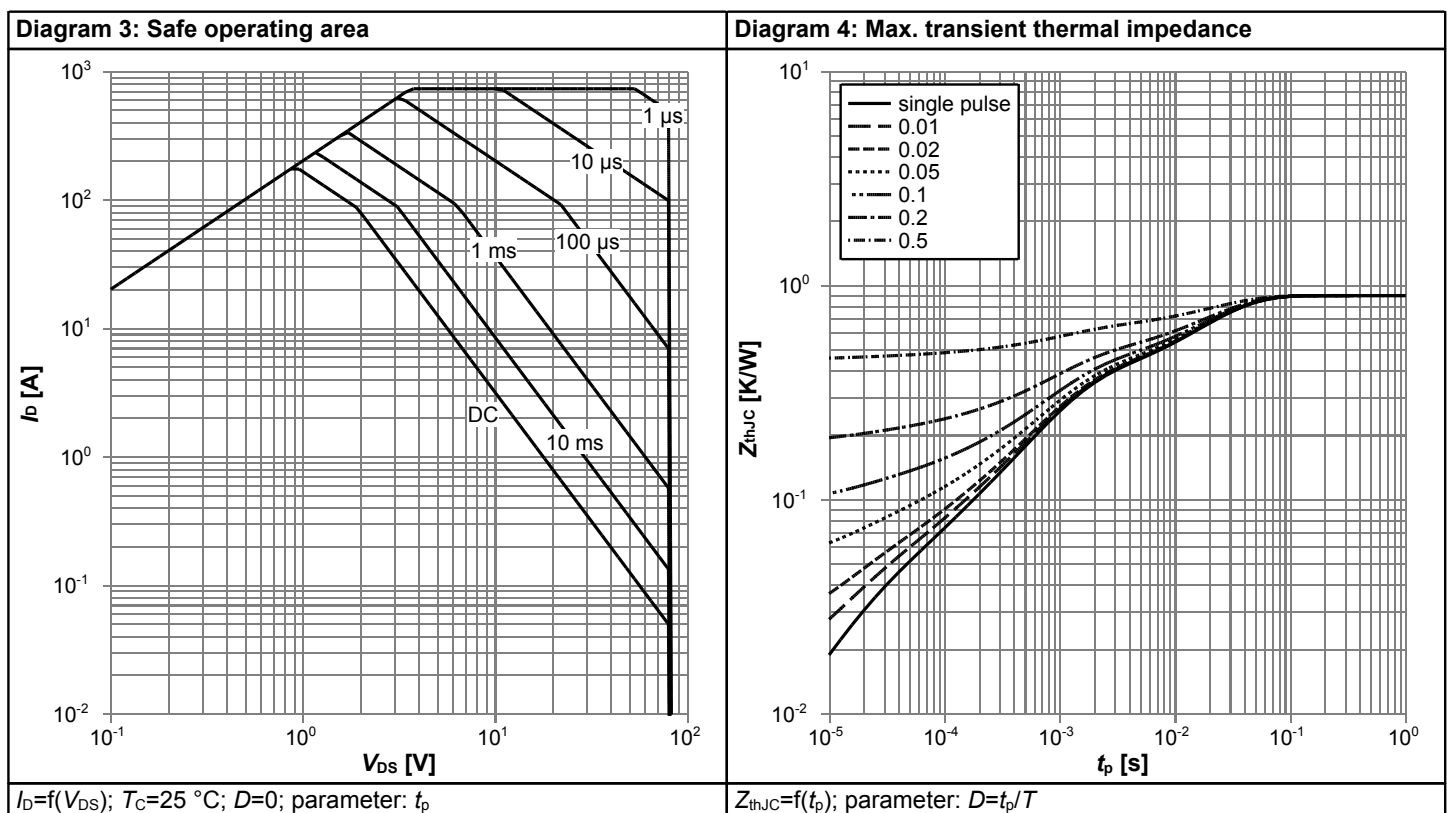
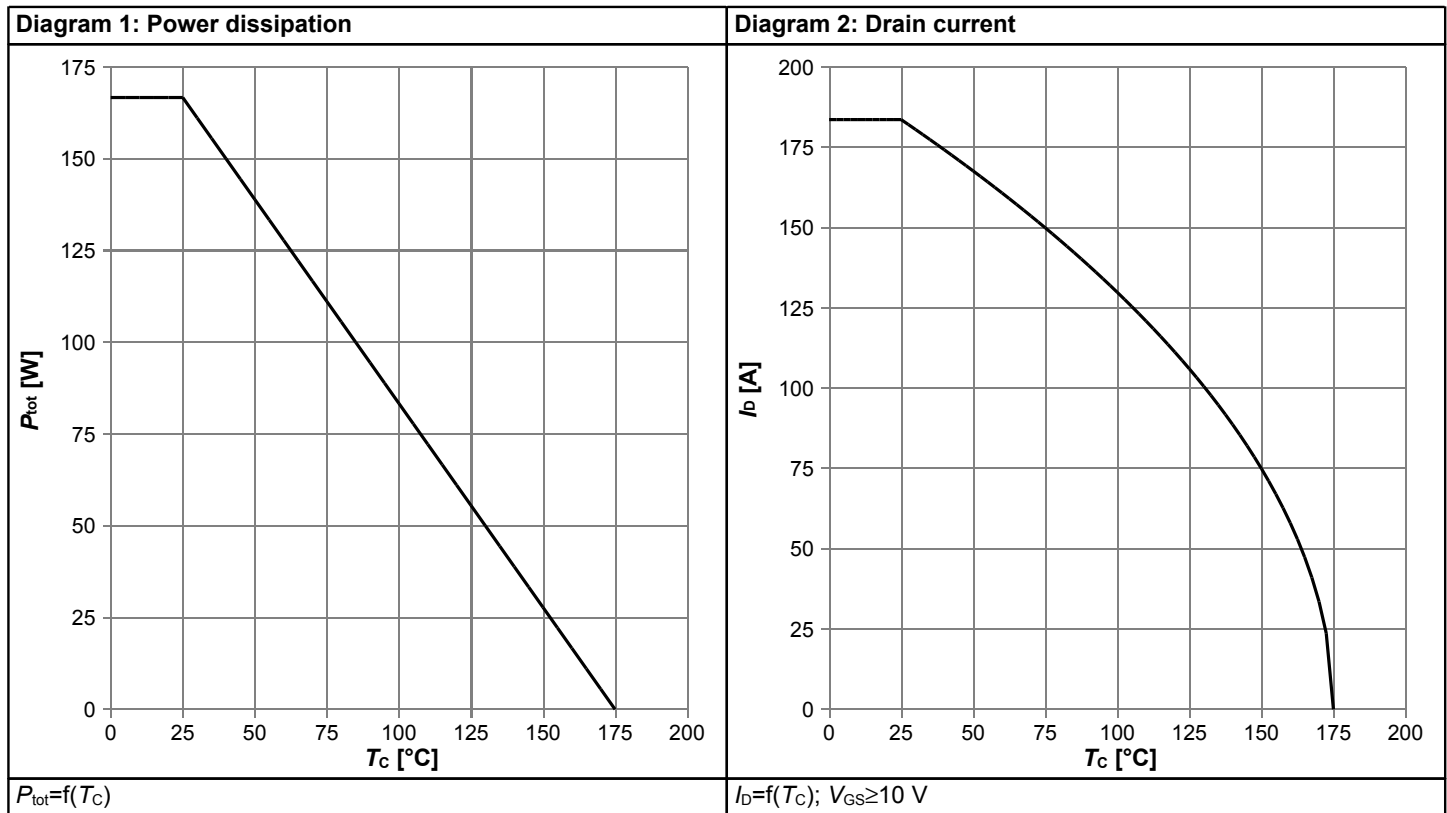
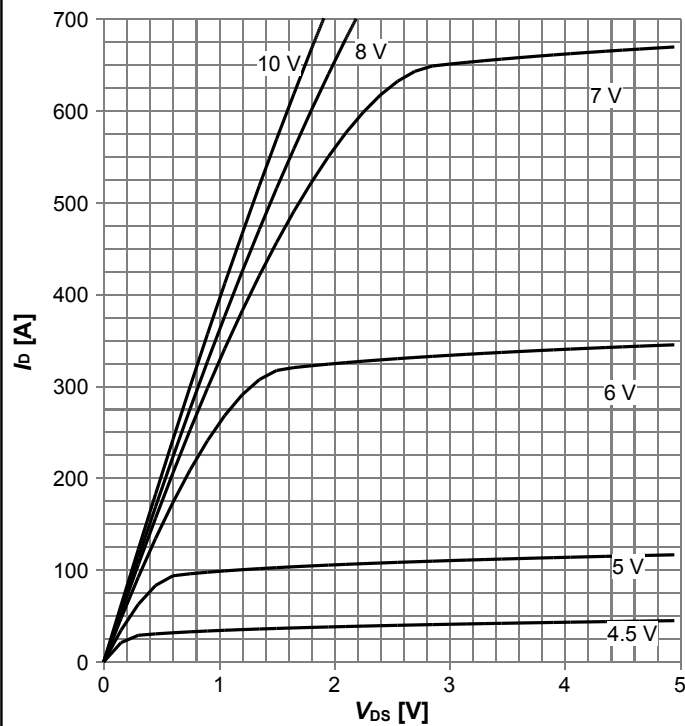
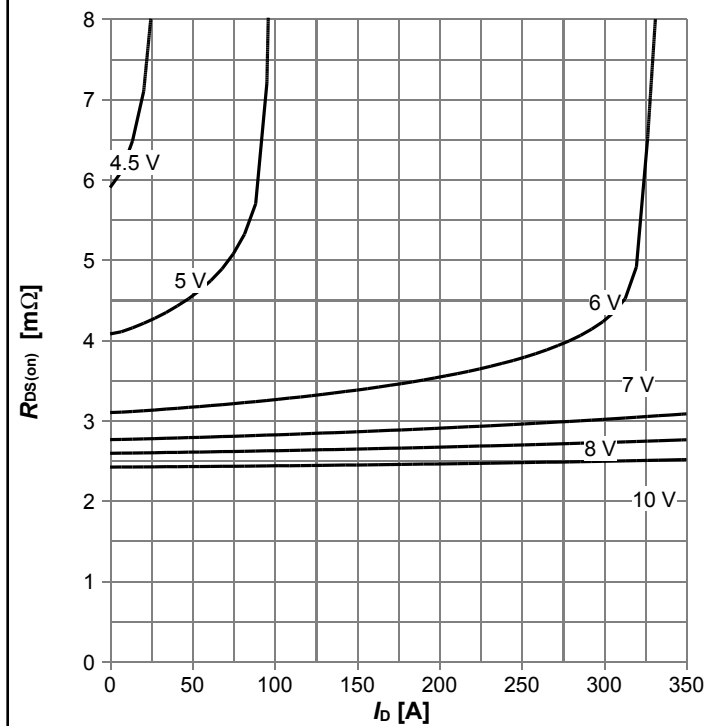


Diagram 5: Typ. output characteristics



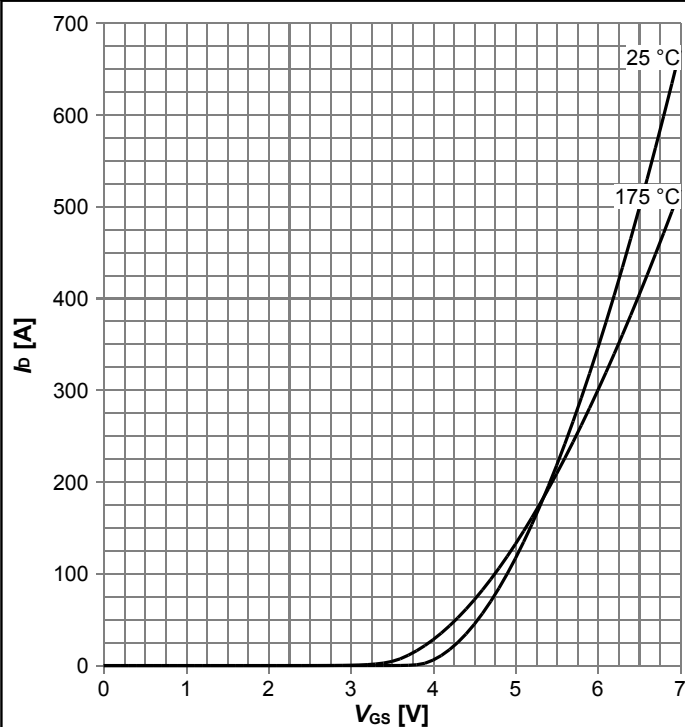
$I_D = f(V_{DS})$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



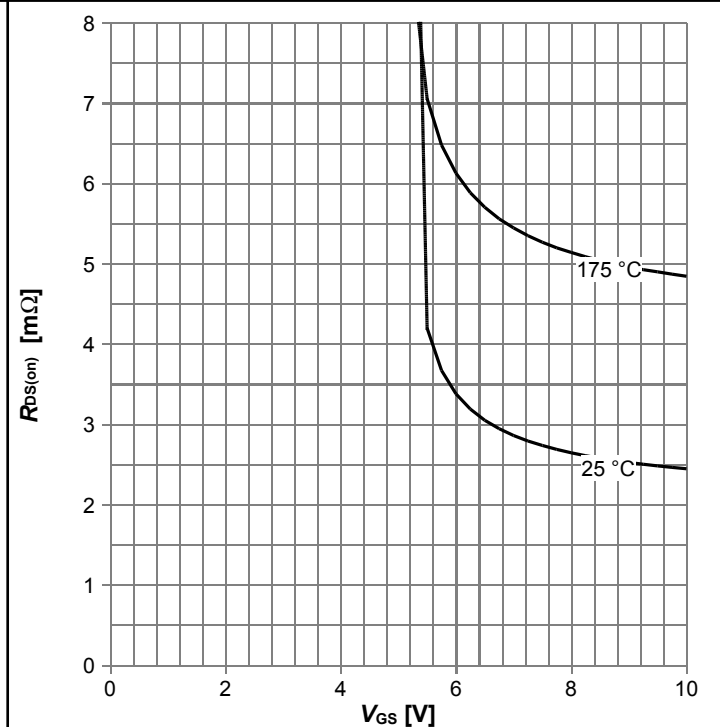
$R_{DS(on)} = f(I_D)$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



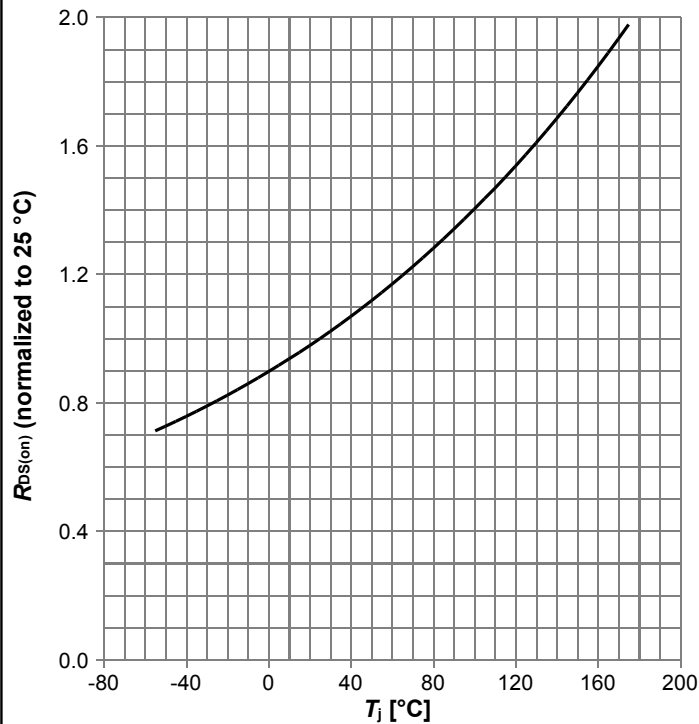
$I_D = f(V_{GS})$ ,  $|V_{DS}| > 2|I_D|R_{DS(on)\max}$ ; parameter:  $T_j$

Diagram 8: Typ. drain-source on resistance



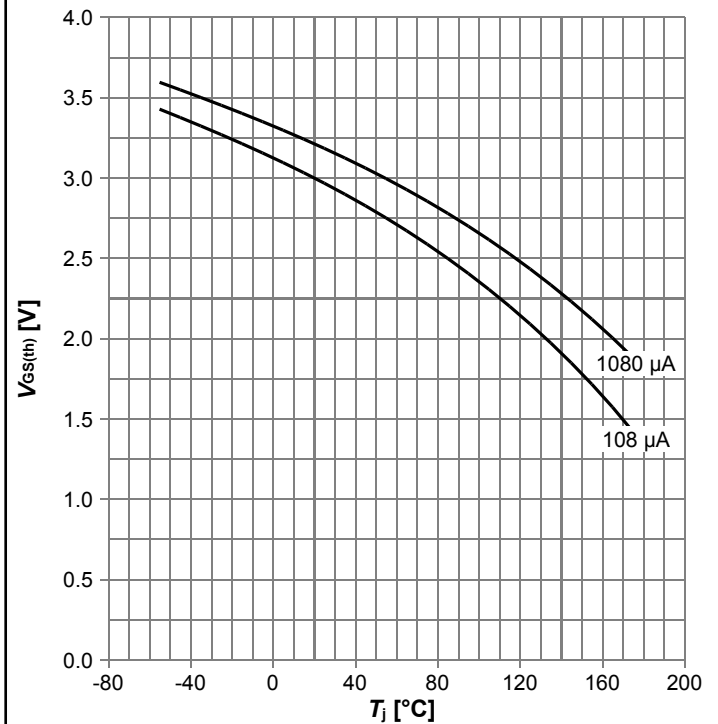
$R_{DS(on)} = f(V_{GS})$ ,  $I_D = 150\text{ A}$ ; parameter:  $T_j$

Diagram 9: Normalized drain-source on resistance



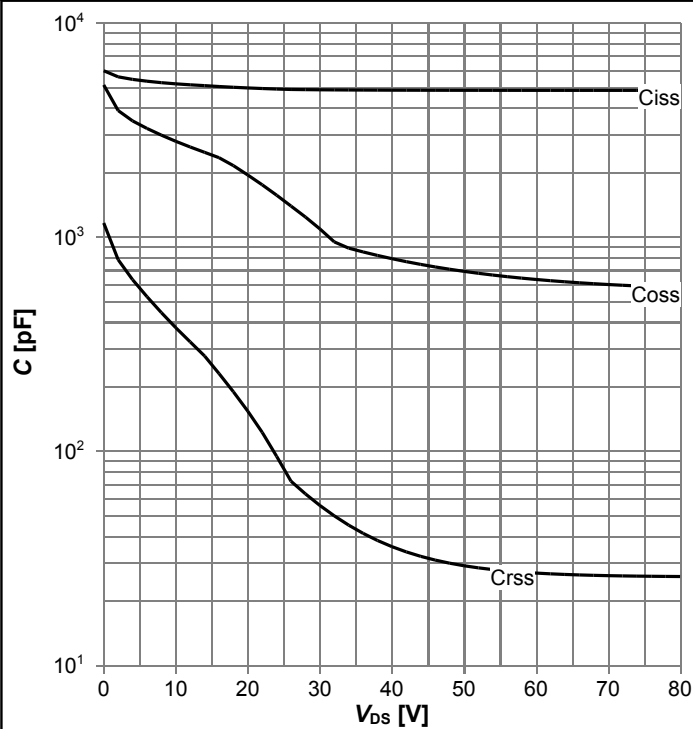
$R_{DS(on)} = f(T_j)$ ,  $I_D = 150$  A,  $V_{GS} = 10$  V

Diagram 10: Typ. gate threshold voltage



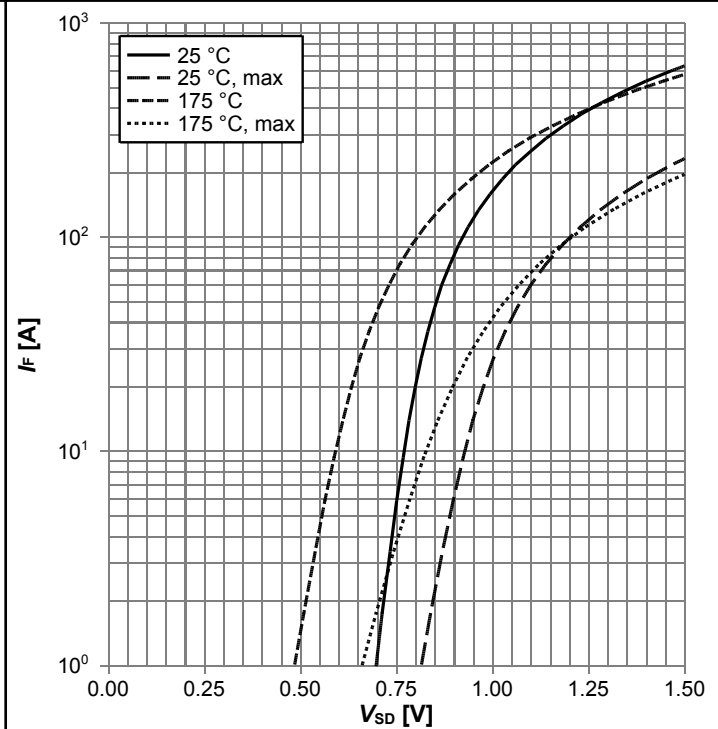
$V_{GS(th)} = f(T_j)$ ,  $V_{GS} = V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



$C = f(V_{DS})$ ;  $V_{GS} = 0$  V;  $f = 1$  MHz

Diagram 12: Forward characteristics of reverse diode



$I_F = f(V_{SD})$ ; parameter:  $T_j$



Diagram 13: Avalanche characteristics

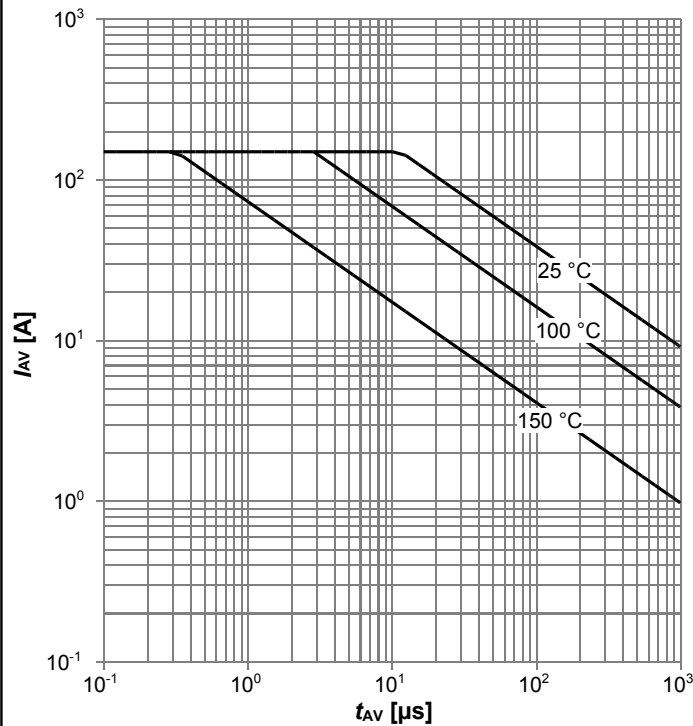


Diagram 14: Typ. gate charge

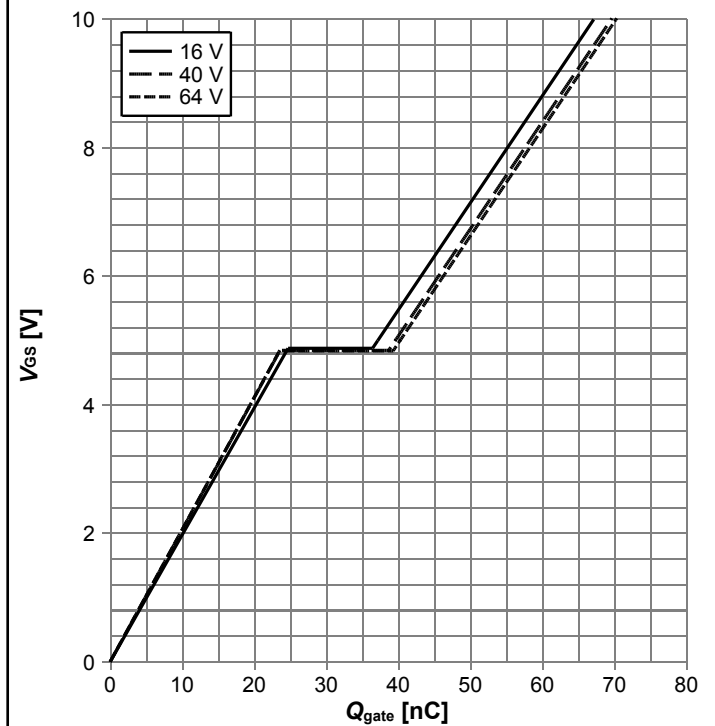


Diagram 15: Drain-source breakdown voltage

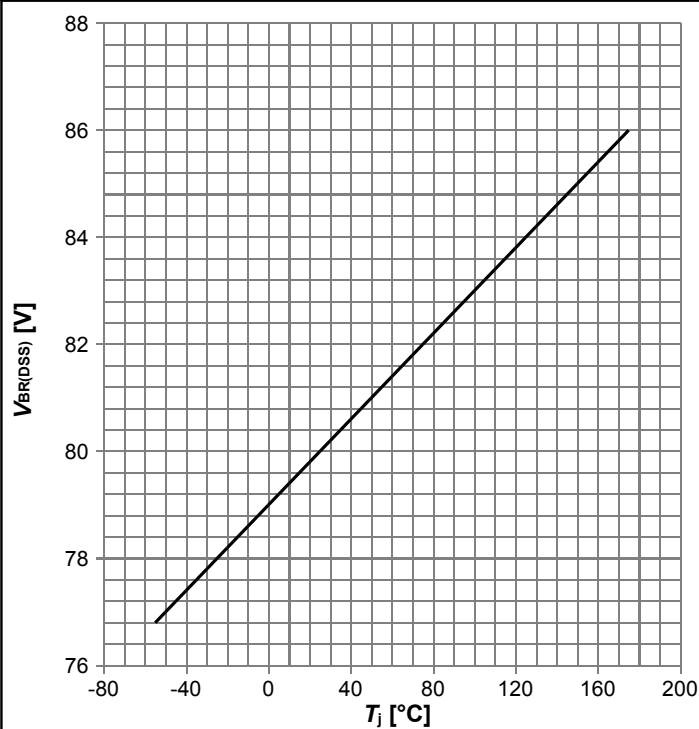
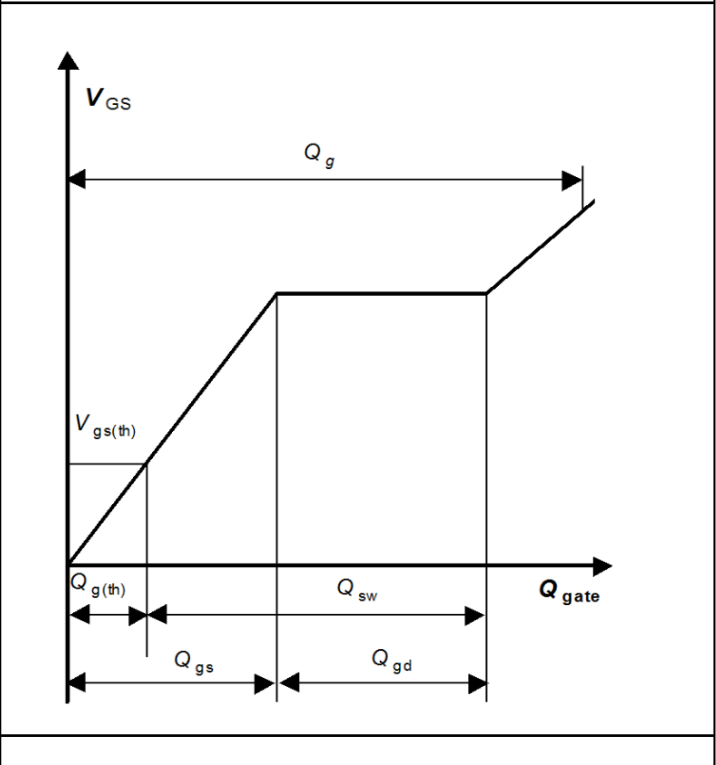
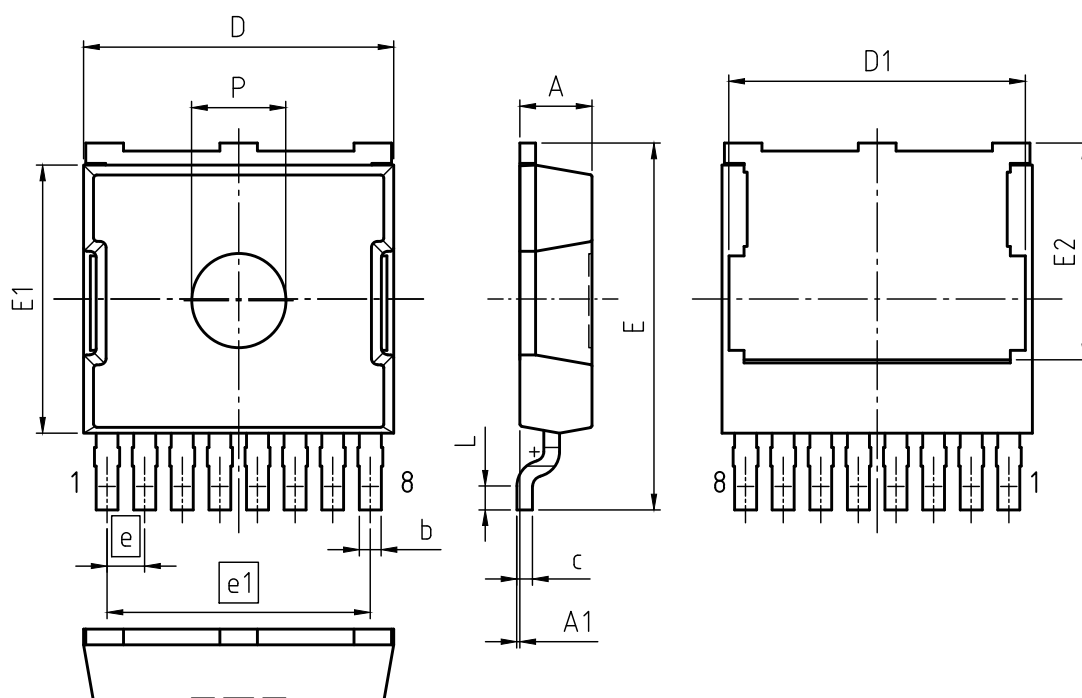


Diagram Gate charge waveforms



## 5 Package Outlines



| PACKAGE - GROUP<br>NUMBER: <b>PG-HSOG-8-U01</b> |             |                  |
|-------------------------------------------------|-------------|------------------|
| REVISION: 01                                    |             | DATE: 08.02.2021 |
| DIMENSIONS                                      | MILLIMETERS |                  |
|                                                 | MIN.        | MAX.             |
| <b>A</b>                                        | 2.20        | 2.40             |
| <b>A1</b>                                       | 0.00        | 0.10             |
| <b>b</b>                                        | 0.60        | 0.80             |
| <b>c</b>                                        | 0.40        | 0.60             |
| <b>D</b>                                        | 9.70        | 10.10            |
| <b>D1</b>                                       | 9.36        | 9.56             |
| <b>E</b>                                        | 11.50       | 11.90            |
| <b>E1</b>                                       | 8.45        | 8.75             |
| <b>E2</b>                                       | 6.81        | 7.01             |
| <b>e</b>                                        | 1.20        |                  |
| <b>e1</b>                                       | 8.40        |                  |
| <b>L</b>                                        | 0.66        | 0.86             |
| <b>P</b>                                        | 2.90        | 3.10             |

**Figure 1** Outline PG-HSOG-8-1, dimensions in mm

## Revision History

IPTG025N08NM5

**Revision: 2021-03-29, Rev. 2.0**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 2.0      | 2021-03-29 | Release of final version                     |

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